

<b>SANYO</b>	No.3252A	2SC4572
	NPN Triple Diffused Planar Silicon Transistor	
800V/20mA Switching Applications		

**Features**

- High breakdown voltage
- Small  $C_{ob}$
- High reliability (Adoption of HVP process)

**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$**

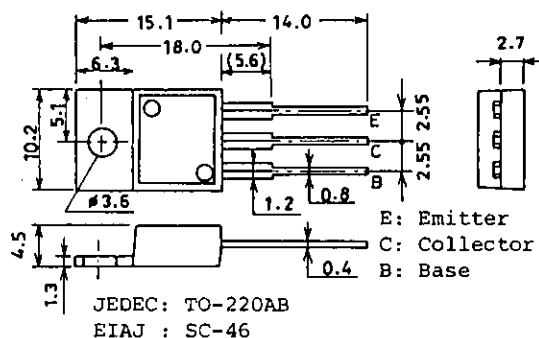
			unit
Collector-to-Base Voltage	$V_{CB0}$	800	V
Collector-to-Emitter Voltage	$V_{CE0}$	800	V
Emitter-to-Base Voltage	$V_{EB0}$	7	V
Collector Current	$I_C$	20	mA
Collector Current (Pulse)	$I_{CP}$	60	mA
Collector Dissipation	$P_C$	1.75	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

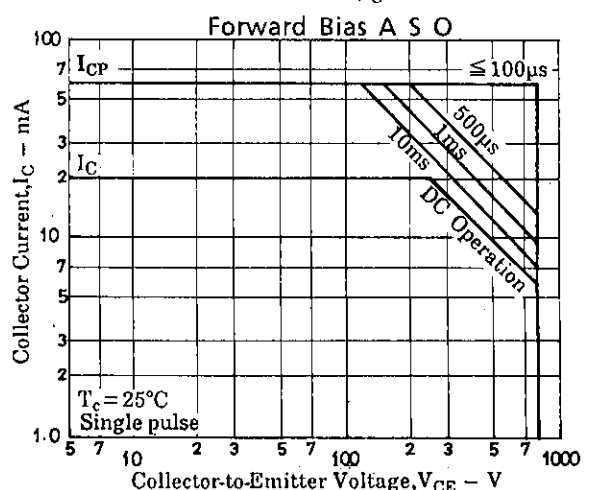
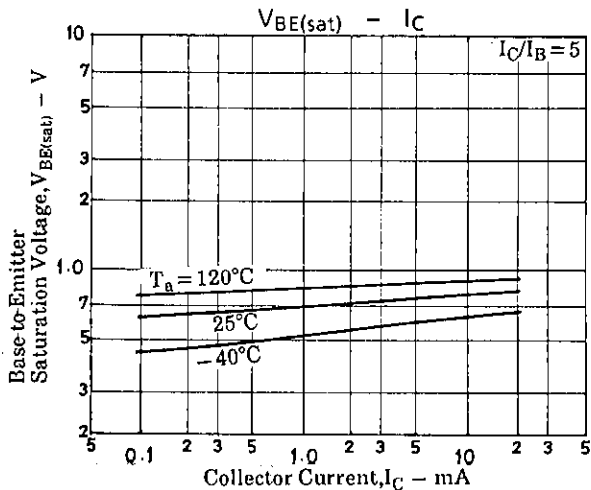
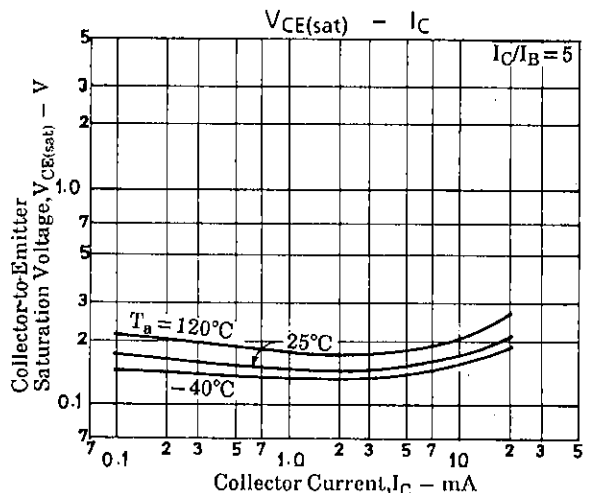
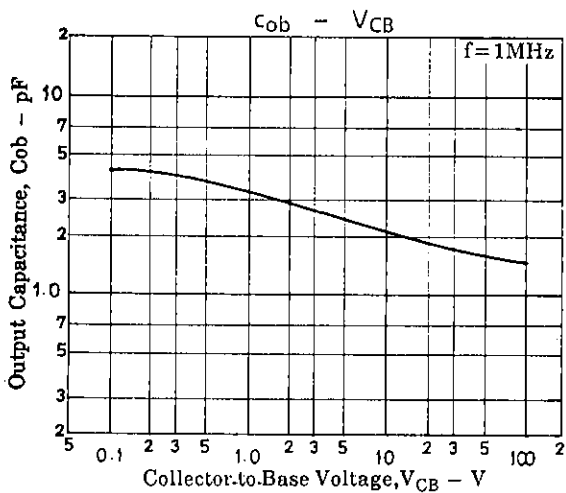
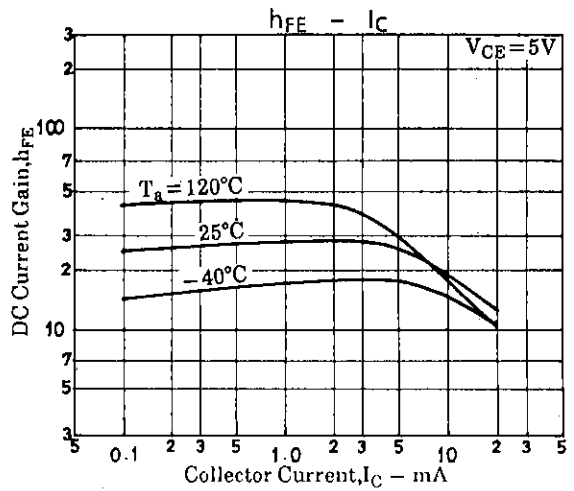
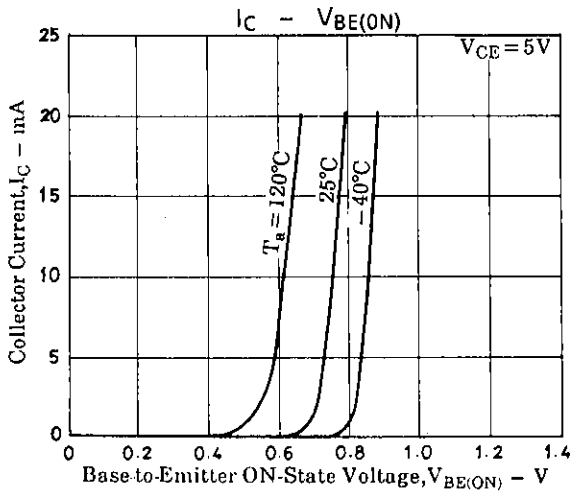
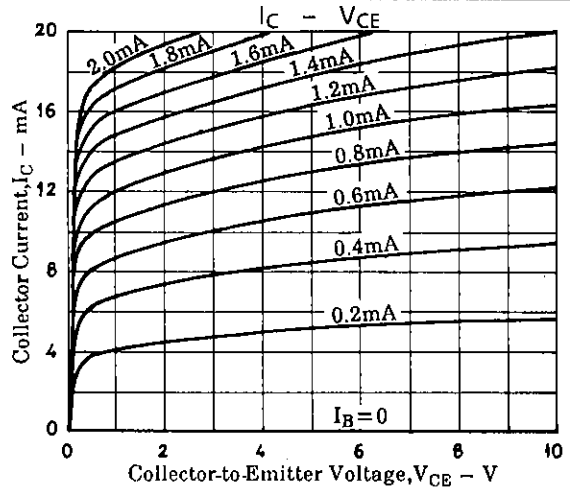
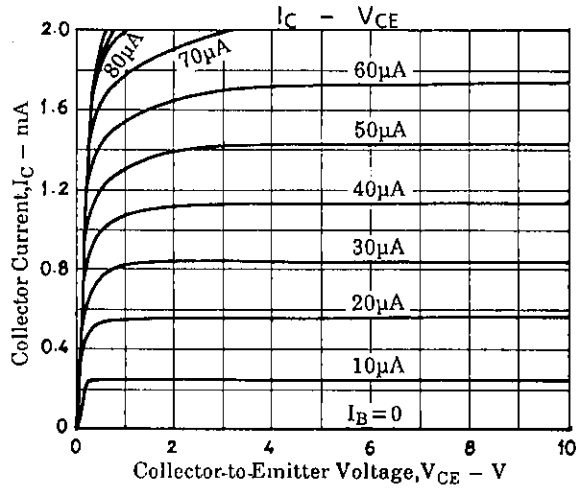
**Electrical Characteristics at  $T_a = 25^\circ\text{C}$**

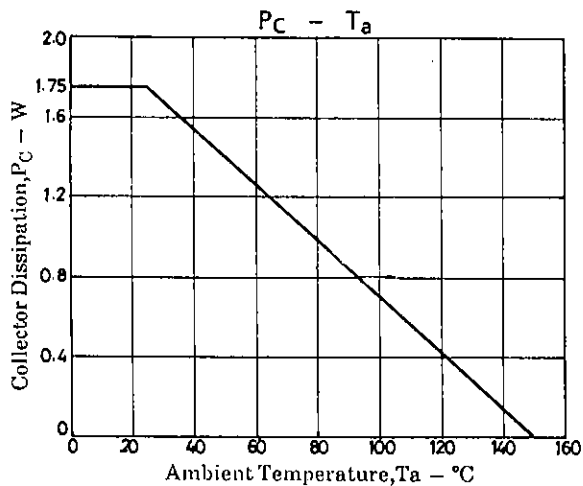
			min	typ	max	unit
Collector Cutoff Current	$I_{CB0}$	$V_{CB} = 800\text{V}, I_E = 0$			1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EB0}$	$V_{EB} = 5\text{V}, I_C = 0$			1	$\mu\text{A}$
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	20		50	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	10			
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}, I_C = 2\text{mA}$		40		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		1.6		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	800			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	7			V
Thermal Resistance	$R_{th(j-c)}$	Junction - Case			8.3	$^\circ\text{C}/\text{w}$

**Package Dimensions 2010B**

(unit: mm)







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